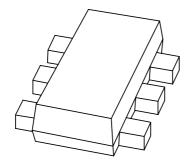
# DISCRETE SEMICONDUCTORS

# DATA SHEET



# **BAT74V**Schottky barrier double diode

Product data sheet 2002 Sep 02



# Schottky barrier double diode

**BAT74V** 

#### **FEATURES**

- Low forward voltage
- Low capacitance
- Ultra small SMD plastic package
- Flat leads: excellent coplanarity and improved thermal behaviour.

#### **APPLICATIONS**

- · Ultra high-speed switching
- Voltage clamping
- · Line termination
- Inverse polarity protection.

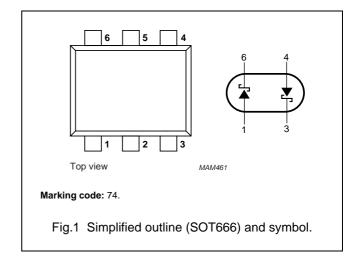
#### **DESCRIPTION**

Planar Schottky barrier double diode with an integrated guard ring for stress protection.

Two separate dies encapsulated in a SOT666 ultra small SMD plastic package.

#### **PINNING**

PIN	DESCRIPTION		
1	anode 1		
2	not connected		
3	cathode 2		
4	anode 2		
5	not connected		
6	cathode 1		



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_R$	continuous reverse voltage		_	30	V
I <sub>F</sub>	continuous forward current		_	200	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p \leq 1 \text{ s; } \delta \leq 0.5$	_	300	mA
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p < 10 \text{ ms}$		600	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	_	230	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

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# Schottky barrier double diode

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#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V <sub>F</sub>	continuous forward voltage	I <sub>F</sub> = 0.1 mA	240	mV
		I <sub>F</sub> = 1 mA	320	mV
		I <sub>F</sub> = 10 mA	400	mV
		I <sub>F</sub> = 30 mA	500	mV
		I <sub>F</sub> = 100 mA; note 1; see Fig.2	800	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 25 V; note 1; see Fig.3	2	μΑ
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; see Fig.4	10	pF

#### Note

1. Pulse test:  $t_p$  = 300  $\mu$ s;  $\delta$  = 0.02.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	416	K/W

#### Note

1. Refer to SOT666 standard mounting conditions.

#### Soldering

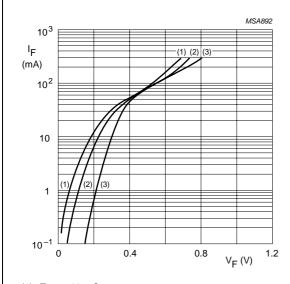
The only recommended soldering method is reflow soldering.

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# Schottky barrier double diode

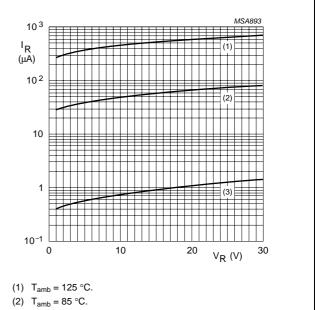
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#### **GRAPHICAL DATA**



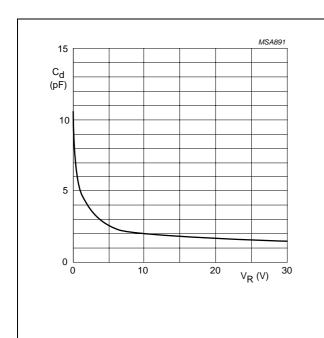
- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.2 Forward current as a function of forward voltage; typical values.



(3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz;  $T_{amb}$  = 25 °C.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

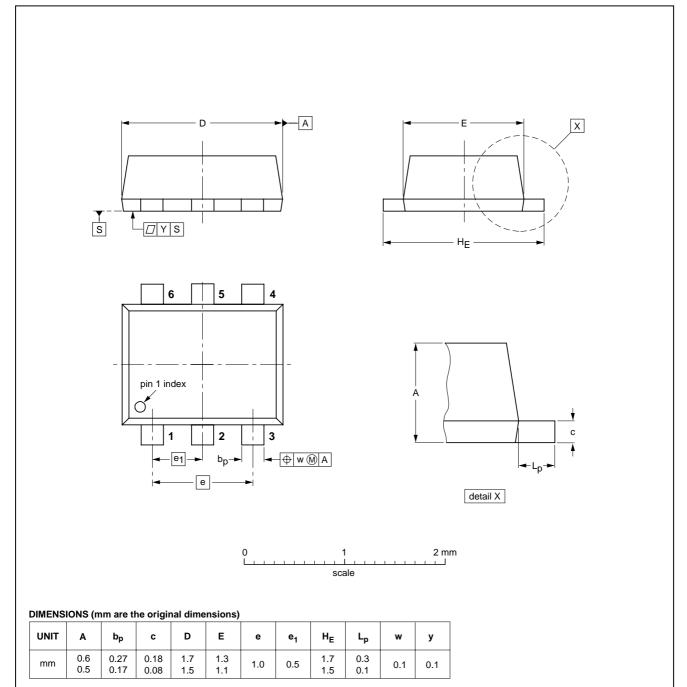
# Schottky barrier double diode

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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						<del>-01-01-04</del> 01-08-27

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### Schottky barrier double diode

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
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